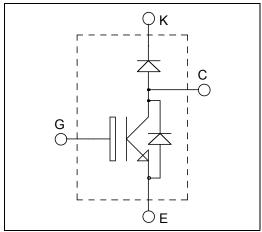
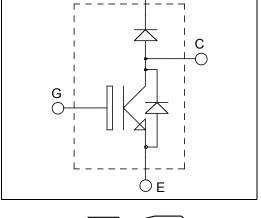


ISOTOP® Boost chopper High speed Trench + Field Stop IGBT4 Power Module

$$V_{CES} = 650V$$
  
 $I_{C} = 50A$  @  $Tc = 80$ °C





## **Application**

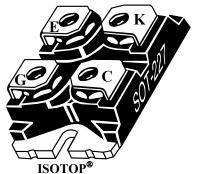
- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

### **Features**

- High speed Trench + Field Stop IGBT 4
  - Low voltage drop
  - Low leakage current
  - Low switching losses
- ISOTOP® Package (SOT-227)
- Very low stray inductance

#### **Benefits**

- Low conduction losses
- Stable temperature behavior
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive  $T_C$  of  $V_{CEsat}$
- **RoHS Compliant**



## All ratings @ $T_i = 25^{\circ}C$ unless otherwise specified

## Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Voltage		650	V
Ţ	Continuous Collector Current	$\Gamma_{\rm C} = 25^{\circ}{\rm C}$	80	
$I_{C}$	$T_C = 80^{\circ}C$	$\Gamma_{\rm C} = 80^{\circ}{\rm C}$	50	A
$I_{CM}$	Pulsed Collector Current	$\Gamma_{\rm C} = 25^{\circ}{\rm C}$	140	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Power Dissipation		220	W

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CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed



## **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 650V$				50	μΑ
17	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $T_{j} = 25^{\circ}C$ $T_{j} = 150^{\circ}C$	1.4	1.85	2.3	V	
$V_{CE(sat)}$	Conector Emitter Saturation Voltage			2.2		V	
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 0.8 \text{ mA}$		4.2	5.1	5.6	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V$ , $V_{CE} = 0V$				150	nA

**Dynamic Characteristics** 

•	Claracteristics	T (C 1)		1.0	æ	17	<b>T</b> T •,
	Characteristic	Test Conditions	3	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			3100		
Coes	Output Capacitance	$V_{CE} = 25V$			116		pF
$C_{res}$	Reverse Transfer Capacitance	f = 1MHz	f = 1MHz				
$Q_{G}$	Gate charge	$V_{GE} = 15V, I_{C} = V_{CE} = 480V$	50A		315		nC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	hing (25°C)		19		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 400V$			33		ns
$T_{d(off)}$	Turn-off Delay Time	$I_C = 50A$			197		115
$T_{\rm f}$	Fall Time	$R_G = 7\Omega$		21			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C)			19		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			29		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 400V$ $I_{\text{C}} = 50A$			227		
$T_{\mathrm{f}}$	Fall Time	$R_G = 7\Omega$			22		
Eon	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 400V$	$T_j = 150$ °C		1.2		mJ
$E_{\text{off}}$	Turn off Energy	$I_{C} = 50A$ $R_{G} = 7\Omega$	$T_j = 150$ °C		1		1113
$I_{sc}$	Short Circuit data	$V_{GE} \le 15V ; V_{Bu}$ $t_p \le 5\mu s ; T_j = 15$			350		A
$R_{thJC}$	Junction to Case Thermal Resistance					0.68	°C/W

**Chopper diode ratings and characteristics** 

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage					650	V
$I_{RM}$	Reverse Leakage Current	$V_R = 650V$				50	μΑ
$I_F$	DC Forward Current		$Tc = 25^{\circ}C$		50		A
$V_{F}$	Diode Forward Voltage	$I_F = 50A$ $V_{GE} = 0V$	$T_i = 25^{\circ}C$ $T_i = 150^{\circ}C$		1.6 1.5	2	V
$t_{rr}$	Reverse Recovery Time	$I_{F} = 50A \\ V_{R} = 300V \\ di/dt = 1800A/\mu s$	$T_j = 25^{\circ}C$ $T_i = 150^{\circ}C$		100 150		ns
Q <sub>rr</sub>	Reverse Recovery Charge		$T_{j} = 25^{\circ}C$ $T_{i} = 150^{\circ}C$		2.6 5.4		μС
E <sub>rr</sub>	Reverse Recovery Energy		$T_j = 25^{\circ}C$ $T_j = 150^{\circ}C$		0.6		mJ
$R_{thJC}$	Junction to Case Thermal Resistance	•	•			1.14	°C/W



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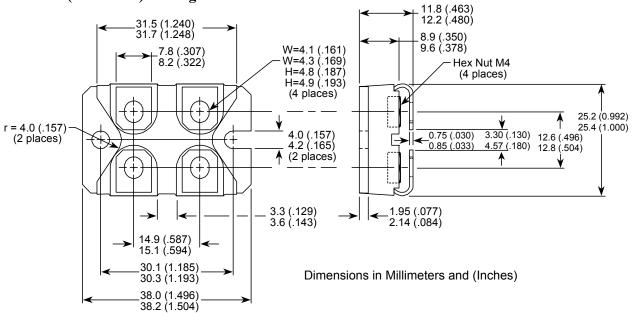
IGBT parallel diode ratings and	characteristics
Combal Changetonistic	Tost Conditions

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage					650	V
$I_{RM}$	Reverse Leakage Current	$V_R = 650V$				50	μΑ
$I_{F}$	DC Forward Current		$Tc = 60^{\circ}C$		20		A
$V_{\mathrm{F}}$	Diode Forward Voltage	$I_F = 20A$ $V_{GE} = 0V$	$T_i = 25$ °C $T_i = 150$ °C		1.6	2	V
t <sub>rr</sub>	Reverse Recovery Time	$I_F = 20A$ $V_R = 300V$ $di/dt = 1600A/\mu s$	$T_j = 25^{\circ}C$ $T_i = 150^{\circ}C$		100 150		ns
Qrr	Reverse Recovery Charge		$T_{j} = 25^{\circ}C$ $T_{i} = 150^{\circ}C$		1.1		μС
Err	Reverse Recovery Energy		$T_j = 25^{\circ}C$ $T_j = 150^{\circ}C$		0.23 0.50		mJ
$R_{thJC}$	Junction to Case Thermal Resistance	•	•			2.6	°C/W

Thermal and package characteristics

Symbol	Characteristic	Min	Тур	Max	Unit
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz	2500			V
$T_J, T_{STG}$	Storage Temperature Range	-55		175	
$T_{JOP}$	Recommended junction temperature under switching conditions	-55		T <sub>J</sub> max -25	°C
$T_{ m L}$	Max Lead Temp for Soldering:0.063" from case for 10 sec			300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)			1.5	N.m
Wt	Package Weight		29.2		g

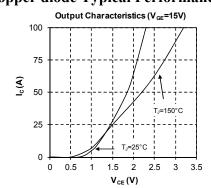
## **SOT-227 (ISOTOP®) Package Outline**

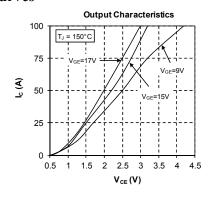


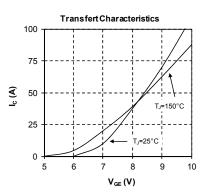
ISOTOP® is a registered trademark of ST Microelectronics NV

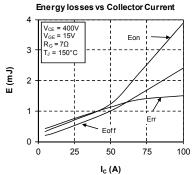


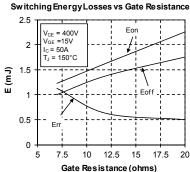
## IGBT & Chopper diode Typical Performance Curves

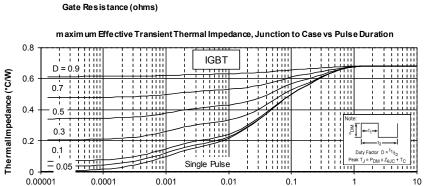










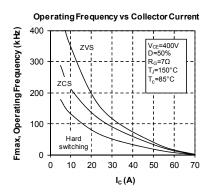


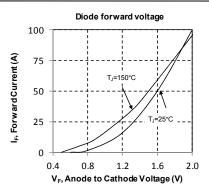
Rectangular Pulse Duration in Seconds

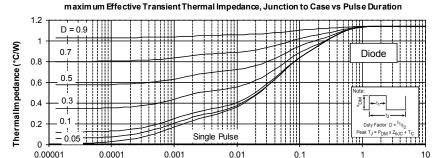
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## Power Matters.™

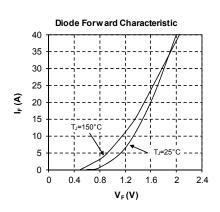


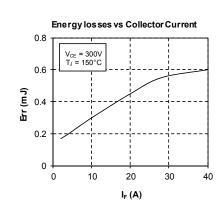


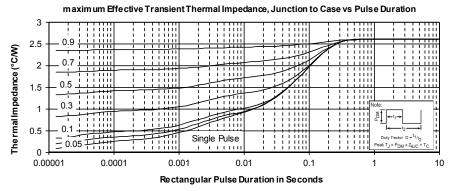


Rectangular Pulse Duration in Seconds

## **IGBT** parallel diode Typical Performance Curves







APT50GLQ65JU2 - Rev 0 August, 2016



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